

# COS/MOS INTEGRATED CIRCUIT

4063B

HCC/HCF 4063B

## 4-BIT MAGNITUDE COMPARATOR

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARD B-SERIES OUTPUT DRIVE
- EXPANSION TO 8-16V ..... 4N BITS BY CASCADING UNITS
- MEDIUM SPEED OPERATION: COMPARES TWO 4-BIT WORDS IN 250 ns (TYP.) AT 10V
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

The **HCC 4063B** (extended temperature range) and **HCF 4063B** (intermediate temperature range) are available in 16-lead dual in-line plastic or ceramic package, ceramic flat package and plastic micropackage. The **HCC/HCF 4063B** is a low-power 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to" or "greater than" a second 4-bit word. The **HCC/HCF 4063B** has eight comparing inputs (A3, B3, through A0, B0), three outputs (A < B, A = B, A > B) and three cascading inputs (A < B, A = B, A > B) that permit systems designers to expand the comparator function to 8, 12, 16 . . . 4N bits. When a single **HCC/HCF 4063B** is used, the cascading inputs are connected as follows: (A < B) = low, (A = B) = high, (A > B) = low.

For words longer than 4 bits, **HCC/HCF 4063B** devices may be cascaded by connecting the outputs of the less-significant comparator to the corresponding cascading inputs of the more-significant comparator. Cascading inputs (A < B, A = B, and A > B) on the least significant comparator are connected to a low, a high, and a low level, respectively.

## ABSOLUTE MAXIMUM RATINGS

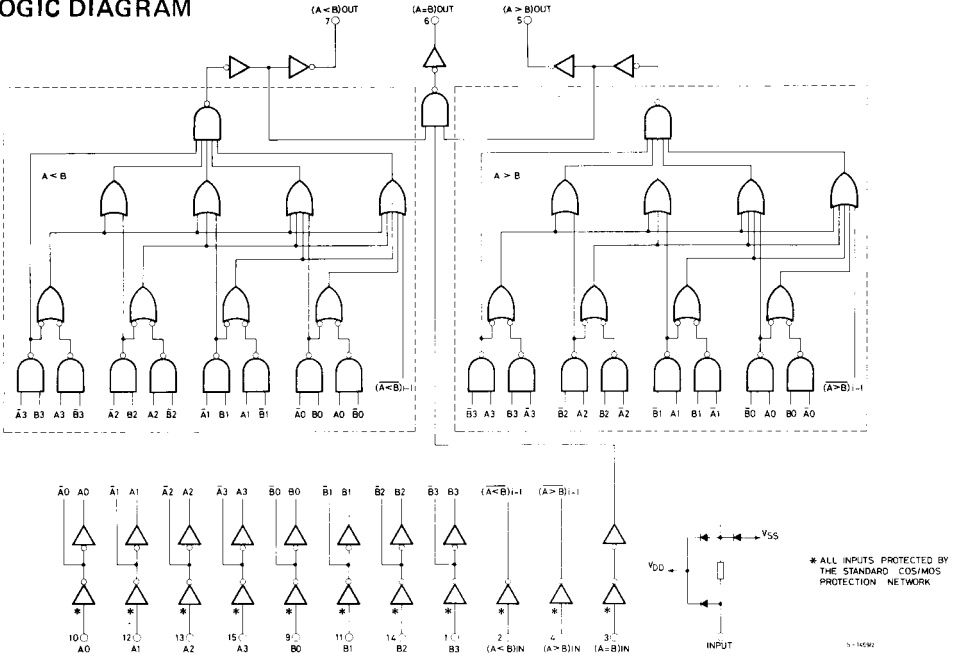
$V_{DD}^*$	Supply voltage: <b>HCC</b> types <b>HCF</b> types	-0.5 to 20 -0.5 to 18	V V
$V_i$	Input voltage	-0.5 to $V_{DD} + 0.5$	V
$I_i$	DC input current (any one input)	$\pm 10$	mA
$P_{tot}$	Total power dissipation (per package) Dissipation per output transistor for $T_{op}$ = full package-temperature range	200 100	mW mW
$T_{op}$	Operating temperature: <b>HCC</b> types <b>HCF</b> types	-55 to 125 -40 to 85	°C °C
$T_{stg}$	Storage temperature	-65 to 150	°C

\* All voltage values are referred to  $V_{SS}$  pin voltage

## ORDERING NUMBERS:

- HCC 4063 BD for dual in-line ceramic package
- HCC 4063 BF for dual in-line ceramic package, frit seal
- HCC 4063 BK for ceramic flat package
- HCF 4063 BE for dual in-line plastic package
- HCF 4063 BF for dual in-line ceramic package, frit seal
- HCF 4063 BM for plastic micropackage



**LOGIC DIAGRAM**

**TRUTH TABLE**

INPUTS							OUTPUTS		
COMPARING				CASCADING					
A3, B3	A2, B2	A1, B1	A0, B0	A < B	A = B	A > B	A < B	A = B	A > B
A3 > B3	X	X	X	X	X	X	0	0	1
A3 = B3	A2 > B2	X	X	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 > B1	X	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	0	1	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	1	0	0	1	0
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	0	0	1	0	0
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	1	0	0
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	1	0	0
A3 = B3	A2 < B2	X	X	X	X	X	1	0	0
A3 < B3	X	X	X	X	X	X	1	0	0

X = Don't care  
 1 ≡ High state  
 0 ≡ Low state

**RECOMMENDED OPERATING CONDITIONS**

V <sub>DD</sub>	Supply voltage: HCC types HCF types	3 to 18 V 3 to 15 V
V <sub>I</sub>	Input voltage	0 to V <sub>DD</sub> V
T <sub>op</sub>	Operating temperature: HCC types HCF types	-55 to 125 °C -40 to 85 °C

*Comp*

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Parameter		Test conditions				Values						Unit		
		V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   ( $\mu$ A)	V <sub>DD</sub> (V)	T <sub>Low</sub> *		25°C			T <sub>High</sub> *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I <sub>L</sub>	Quiescent current	HCC types	0/ 5			5		5	0.04	5		150	$\mu$ A	
			0/10			10		10	0.04	10		300		
			0/15			15		20	0.04	20		600		
			0/20			20		100	0.08	100		3000		
	HCF types	0/ 5			5		20	0.04	20		150			
		0/10			10		40	0.04	40		300			
	0/15			15		80	0.04	80		600				
V <sub>OH</sub>	Output high voltage	0/ 5		< 1	5	4.95		4.95			4.95	V		
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V <sub>OL</sub>	Output low voltage	5/0		< 1	5		0.05		0.05		0.05	V		
		10/0		< 1	10		0.05		0.05		0.05			
		15/0		< 1	15		0.05		0.05		0.05			
V <sub>IH</sub>	Input high voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V <sub>IL</sub>	Input low voltage		4.5/0.5	< 1	5		1.5		1.5		1.5	V		
			9/1	< 1	10		3		3		3			
			13.5/1.5	< 1	15		4		4		4			
I <sub>OH</sub>	Output drive current	HCC types	0/ 5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/ 5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF types	0/ 5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/ 5	4.6		5	-0.52		-0.44	-1		-0.36		
	0/10	9.5		10	-1.3		-1.1	-2.6		-0.9				
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4				
I <sub>OL</sub>	Output sink current	HCC types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input leakage current	HCC types	0/18	Any input		18		$\pm$ 0.1		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.1		$\pm$ 1	$\mu$ A
		HCF types	0/15			15		$\pm$ 0.3		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.3		$\pm$ 1	
C <sub>i</sub>	Input capacitance			Any input					5	7.5			pF	

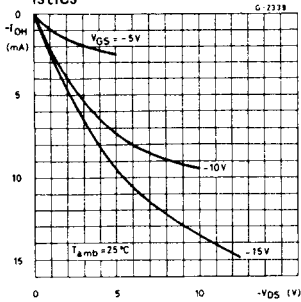
\* T<sub>Low</sub> = - 55°C for HCC device; -40°C for HCF device.  
 \* T<sub>High</sub> = +125°C for HCC device; +85°C for HCF device.  
 The Noise Margin for both "1" and "0" level is: 1V min. with V<sub>DD</sub>= 5V  
 2V min. with V<sub>DD</sub>= 10V  
 2.5V min. with V<sub>DD</sub>= 15V

## DYNAMIC ELECTRICAL CHARACTERISTICS

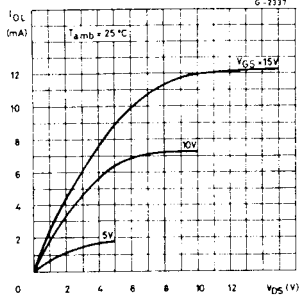
( $T_{amb} = 25^{\circ}\text{C}$ ,  $C_L = 50\text{ pF}$ ,  $R_L = 200\text{ k}\Omega$ , typical temperature coefficient for all  $V_{DD}$  values is  $0.3\%/^{\circ}\text{C}$ , all input rise and fall times =  $20\text{ ns}$ )

Parameter	Test conditions	Values			Unit	
		$V_{DD}$ (V)	Min.	Typ.		Max.
$t_{PLH}$ , $t_{PHL}$ Propagation delay time	Comparing inputs to outputs	5		625	1250	ns
		10		250	500	
		15		175	350	
	Cascading inputs to outputs	5		500	1000	
		10		200	400	
		15		140	280	
$t_{TLH}$ Transition time $t_{THL}$		5		100	200	ns
		10		50	100	
		15		40	80	

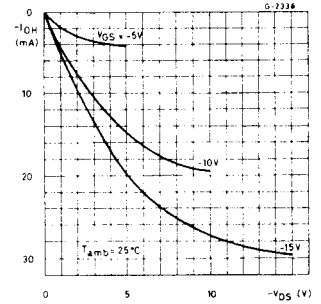
Minimum output high (source) current characteristics



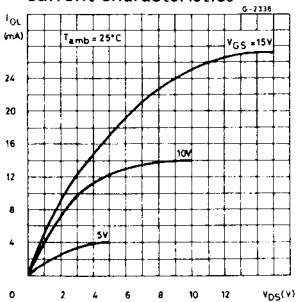
Minimum output low (sink) current characteristics



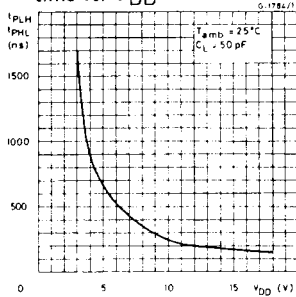
Typical output high (source) current characteristics



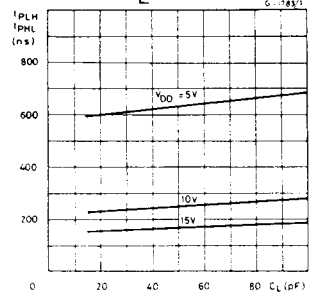
Typical output low (sink) current characteristics



Typical propagation delay time vs.  $V_{DD}$

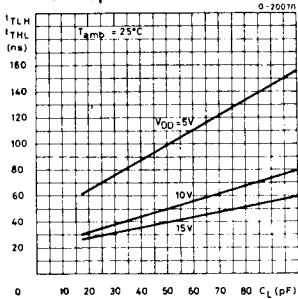


Typical propagation delay time vs.  $C_L$

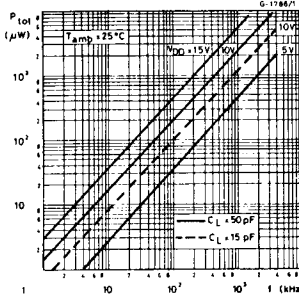


# HCC/HCF 4063B

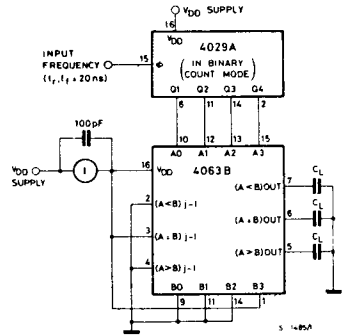
Typical transition time vs. load capacitance



Typical power dissipation characteristics

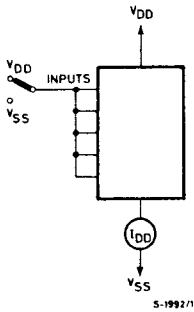


Dynamic power dissipation

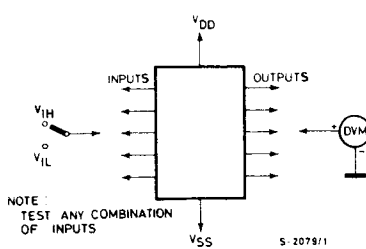


## TEST CIRCUITS

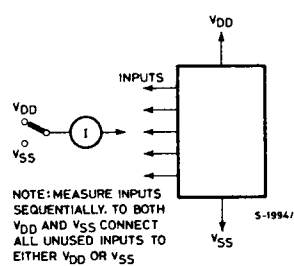
Quiescent device current



Noise immunity

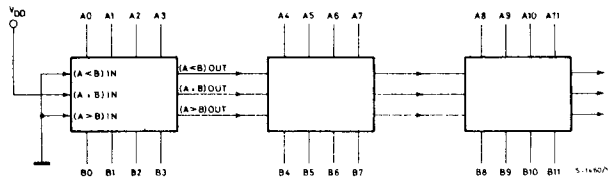


Input leakage current



## TYPICAL APPLICATION

Typical speed characteristics of a 12-bit comparator



$$t_p (\text{TOT.}) = t_p (\text{COMPARE INPUTS}) + 2 \times t_p (\text{CASCADE INPUTS}) \text{ at } C_L = 50 \text{ pF (each output), } V_{DD} = 10\text{V (3 stages)}$$

$$= 250 + 2 \times (200) = 650 \text{ ns (typ.)}$$